♣.

REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 6- 34 are now pending in this application. Claims 6-10 are amended. Claims 11-24 are added. Support for the amendment of claim 1 is found at least at page 5, lines 10-15. Support for the added claims is found at least at page 5, line 26 through page 6, line 6. No new matter is added.

In the outstanding Office Action, Claims 6-10 were rejected under 35 U.S.C. § 102(e) as anticipated by <u>Rocha-Alvarez</u>, U.S. 6,797,643. In response, claim 6 is amended to clarify that the starting material silane is an alkoxydisilane.

As amended, claim 6 is directed to a method for making a silicon oxide film. The method includes forming a silicon oxide film by thermochemical vapor-phase deposition at a pressure of 0.01mmHg to 2 atm using an alkoxydisilane compound of the specified formula. Claims 7-24 all depend from directly or indirectly from claim 6.

Applicants respectfully note that the presently claimed method features a process using an alkoxydisilane compound. Alkoxydisilane compounds have the general formula $H_n Si_2 \ (OR)_{6\text{-}n} \ .$

Thus, alkoxydisilanes are characterized by a pair of silicon atoms bound together, with at least one alkoxyl group joined thereto.

Rocha-Alvarez discloses a method of making a film on a substrate in which one or more organosilicon compounds, one or more aliphatic compounds, and one or more oxidizing gases are reacted in a gas mixture in the presence of an electric field. Rocha-Alvarez discloses a long list of aliphatic and cyclic organosilicon compounds that are used in the method. However, Rocha-Alvarez does not disclose any alkoxydisilane compounds. Indeed,

Application No. 10/589,077

Reply to Office Action of June 23, 2008

the only disilane compound disclosed by <u>Rocha-Alvarez</u> is hexamethyldisilane, which clearly lacks an alkoxyl group.

In order to anticipate, a single reference must disclose, explicitly or inherently, all of the elements of the claimed invention. Because <u>Rocha-Alvarez</u> fails to disclose any process of making a silicon oxide film using an alkoxydisilane compound, <u>Rocha-Alvarez</u> cannot anticipate claim 6. Accordingly, Applicants respectfully request withdrawal of the rejections of claim 6 and all of the claims depending therefrom.

In light of the above discussion, the present application is believed to be in condition for allowance. An early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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